

2829



PATENT
30205/37916

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Jae Hong Kim and
Sang Ick Lee

Serial No.: 10/038,375

Filed: January 4, 2002

For: Chemical Mechanical Polishing
Slurry and Process for Ruthenium Films

Group Art Unit: 2829

Examiner: Asok K. Sarkar

I hereby certify that this paper and the documents referred to as enclosed therewith are being deposited with the United States Postal Service as first class mail, postage prepaid, on January 21, 2003, in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231.

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the office action mailed on October 22, 2002, please amend the above-identified patent application, as follows:

In the Specification:

Please replace the paragraph beginning on page 6, line 8, with the following rewritten paragraph:

--In more detail, the slurry containing about 2 wt% of HNO₃ and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 600 Å/min under a polishing pressure of 1 psi; the slurry containing about 2 wt% of HNO₃ and about 6 wt% of ceric ammonium nitrate has a polishing rate of about 1200 Å/min under a polishing pressure of 1 psi; the slurry containing about 2 wt% of HNO₃ and about 10 wt% of ceric ammonium nitrate has a polishing rate of about 1400 Å/min under a polishing pressure of 1 psi; the slurry containing about 6 wt% of HNO₃ and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 1050 Å/min under a polishing pressure of 1 psi; and the slurry containing about 10 wt% of HNO₃ and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 1200 Å/min under a polishing pressure of 1 psi.--

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